

# S Bin Anooz

## List of Publications by Year in descending order

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45  
papers

717  
citations

623734

14  
h-index

552781

26  
g-index

45  
all docs

45  
docs citations

45  
times ranked

717  
citing authors

#	ARTICLE	IF	CITATIONS
1	Lateral 1.8 kV $\text{Ga}_2\text{O}_3$ MOSFET With 155 MW/cm <sup>2</sup> Power Figure of Merit. IEEE Electron Device Letters, 2019, 40, 1503-1506.	3.9	104
2	Influence of strontium doping on the indirect band gap and optical constants of ammonium zinc chloride crystals. Physica B: Condensed Matter, 2003, 327, 43-54.	2.7	80
3	Step-flow growth in homoepitaxy of $\text{Ga}_2\text{O}_3$ (100) – The influence of the miscut direction and faceting. APL Materials, 2019, 7, .	5.1	73
4	Step flow growth of $\text{Ga}_2\text{O}_3$ thin films on vicinal (100) $\text{Ga}_2\text{O}_3$ substrates grown by MOVPE. Applied Physics Letters, 2020, 116, .	3.3	59
5	Bulk single crystals of $\text{Ga}_2\text{O}_3$ and Ga-based spinels as ultra-wide bandgap transparent semiconducting oxides. Progress in Crystal Growth and Characterization of Materials, 2021, 67, 100511.	4.0	47
6	Strain-induced phase transitions in epitaxial $\text{NaNbO}_3$ thin films grown by metal-organic chemical vapour deposition. Journal of Applied Crystallography, 2012, 45, 1015-1023.	4.5	40
7	Two inch diameter, highly conducting bulk $\text{Ga}_2\text{O}_3$ single crystals grown by the Czochralski method. Applied Physics Letters, 2022, 120, .	3.3	31
8	Challenges to overcome breakdown limitations in lateral $\text{Ga}_2\text{O}_3$ MOSFET devices. Microelectronics Reliability, 2020, 114, 113951.	1.7	28
9	Impact of chamber pressure and Si-doping on the surface morphology and electrical properties of homoepitaxial (100) $\text{Ga}_2\text{O}_3$ thin films grown by MOVPE. Journal Physics D: Applied Physics, 2021, 54, 034003.	2.8	26
10	Fast homoepitaxial growth of (100) $\text{Ga}_2\text{O}_3$ thin films via MOVPE. AIP Advances, 2021, 11, .	1.3	22
11	The solid state phase transformation of potassium sulfate. Solid State Communications, 2007, 141, 497-501.	1.9	18
12	Optical absorption spectra and related parameters of ammonium zinc chloride crystal in the antiferroelectric and commensurate phases. Crystal Research and Technology, 2003, 38, 798-810.	1.3	17
13	Optical properties of pure and metal ions doped ammonium sulfate single crystals. Crystal Research and Technology, 2006, 41, 487-493.	1.3	15
14	Indium incorporation in homoepitaxial $\text{Ga}_2\text{O}_3$ thin films grown by metal organic vapor phase epitaxy. Journal of Applied Physics, 2019, 125, .	2.5	14
15	Approaching the high intrinsic electrical resistivity of $\text{NbO}_2$ in epitaxially grown films. Applied Physics Letters, 2020, 116, 182103.	3.3	14
16	Impact of epitaxial strain on the ferromagnetic transition temperature of $\text{SrRuO}_3$ thin films. Thin Solid Films, 2011, 519, 6264-6268.	1.8	12
17	$\text{SnO}/\text{Ga}_2\text{O}_3$ heterojunction field-effect transistors and vertical p-n diodes. Applied Physics Letters, 2022, 120, .	3.3	12
18	Growth of epitaxial sodium-bismuth-titanate films by metal-organic chemical vapor phase deposition. Thin Solid Films, 2011, 520, 239-244.	1.8	11

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19	Effects of post-growth annealing on physical properties of SrRuO <sub>3</sub> thin film grown by MOCVD. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2010, 207, 2492-2498.	1.8	10
20	Kinetic Monte Carlo model for homoepitaxial growth of $\text{GaO}_3$ . <i>Physical Review Research</i> , 2020, 2, .	3.6	10
21	Toward Precise n-Type Doping Control in MOVPE-Grown $\text{In}_2\text{-Ga}_2\text{O}_3$ Thin Films by Deep-Learning Approach. <i>Crystals</i> , 2022, 12, 8.	2.2	7
22	Machine learning supported analysis of MOVPE grown $\text{In}_2\text{-Ga}_2\text{O}_3$ thin films on sapphire. <i>Journal of Crystal Growth</i> , 2022, 592, 126737.	1.5	7
23	Spectroscopic ellipsometry studies on the optical constants of Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> :xNa thin films grown by metal-organic chemical vapor deposition. <i>Thin Solid Films</i> , 2011, 519, 3782-3788.	1.8	6
24	Fingerprints of optical absorption in the perovskite LaInO <sub>3</sub> : Insight from many-body theory and experiment. <i>Physical Review B</i> , 2021, 103, .	3.2	6
25	Doping-induced-effects on conduction mechanisms in incommensurate ammonium zinc chloride crystals. <i>Crystal Research and Technology</i> , 2007, 42, 569-577.	1.3	5
26	Structural and transport properties of SrRuO <sub>3</sub> thin films grown by MOCVD on (001) SrTiO <sub>3</sub> substrates: The role of built-in strain and extra phases. <i>Materials Science and Engineering B: Solid-State Materials for Advanced Technology</i> , 2011, 176, 647-652.	3.5	5
27	Refractory metal-based ohmic contacts on $\text{In}_2\text{-Ga}_2\text{O}_3$ using TiW. <i>APL Materials</i> , 2022, 10, .	5.1	5
28	Electron irradiation-induced effects on optical spectra of (NH <sub>4</sub> ) <sub>2</sub> ZnCl <sub>4</sub> : x Sr <sub>2</sub> single crystals. <i>Crystal Research and Technology</i> , 2003, 38, 83-93.	1.3	4
29	The non-isotropic character of electric and dielectric properties of ammonium zinc chloride crystal. <i>Journal of Physics and Chemistry of Solids</i> , 2004, 65, 957-964.	4.0	4
30	Growth and characterization of undoped, Sr <sup>2+</sup> , and Mn <sup>2+</sup> -doped ammonium tetrachlorozincate. <i>Crystal Research and Technology</i> , 2005, 40, 204-211.	1.3	4
31	Deep-level noise characterization of MOVPE-grown $\text{In}_2\text{-Ga}_2\text{O}_3$ . <i>Applied Physics Letters</i> , 2019, 115, .	3.3	4
32	High temperature phase transitions in NaNbO <sub>3</sub> epitaxial films grown under tensile lattice strain. <i>Applied Physics Letters</i> , 2022, 120, .	3.3	4
33	Effect of on the growth and thermal properties of K <sub>2</sub> SO <sub>4</sub> crystal. <i>Journal of Physics and Chemistry of Solids</i> , 2008, 69, 2356-2359.	4.0	3
34	Mechanism of the dc conduction in undoped and Sr <sup>2+</sup> doped ammonium zinc chloride crystal. <i>Solid State Communications</i> , 2004, 129, 797-802.	1.9	2
35	Optical constants of MOCVD-grown Aurivillius phases in the Bi <sub>4</sub> Ti <sub>3</sub> O <sub>12</sub> -Na <sub>0.5</sub> Bi <sub>0.5</sub> TiO <sub>3</sub> system measured by spectroscopic ellipsometry. <i>Applied Physics A: Materials Science and Processing</i> , 2011, 105, 81-88.	2.3	2
36	Refractive index and interband transitions in strain modified NaNbO <sub>3</sub> thin films grown by MOCVD. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 385303.	2.8	2

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37	Effects induced by $\gamma$ -irradiation on intraband transitions in Sr <sup>2+</sup> -doped ammonium zinc chloride crystals. Radiation Effects and Defects in Solids, 2003, 158, 743-755.	1.2	1
38	Mn <sup>2+</sup> -Doping Effects on Commensuration and Incommensuration of Ammonium Zinc Chloride Crystal. Ferroelectrics, 2004, 313, 113-128.	0.6	1
39	Influence of Sr <sup>2+</sup> -Doping, Temperature and Frequency on Dielectric Constant, Dielectric Loss Factor and AC Conductivity of Ammonium Zinc Chloride Crystal. Japanese Journal of Applied Physics, 2005, 44, 1883-1891.	1.5	1
40	Phase transformation kinetics during the heating of an Al <sup>100-8</sup> Li alloy. High Temperatures - High Pressures, 2002, 34, 535-548.	0.3	1
41	Study of electrical and thermal properties of Al <sup>100-x</sup> Li <sub>x</sub> . Materials Science and Technology, 2002, 18, 201-206.	1.6	0
42	Temperature dependence of the indirect band gap and related optical parameters of (NH <sub>4</sub> ) <sub>2</sub> ZnCl <sub>4</sub> :xSr <sup>2+</sup> single crystals. Physica Status Solidi (B): Basic Research, 2003, 240, 246-254.	1.5	0
43	Effects induced by chemical non-stoichiometry and $\gamma$ -irradiation on the habit and unit cell parameters of ammonium tetrachlorozincate. Crystal Research and Technology, 2006, 41, 379-387.	1.3	0
44	Effect on quench rate on the precipitation hardening of Al <sup>100-x</sup> Li <sub>x</sub> binary alloys. High Temperatures - High Pressures, 2003, 35/36, 453-464.	0.3	0
45	Switching behavior and dynamic on-resistance of lateral $\text{In}^{2-}\text{Ga}_{2-}\text{O}_{3-}$ MOSFETs up to 400 V., 2021, , .		0